

Solid State Devices, Inc.

14701 Firestone Blvd * La Mirada, CA 90638 Phone: (562) 404-4474 * Fax: (562) 404-1773 ssdi@ssdi-power.com * www.ssdi-power.com

DESIGNER'S DATA SHEET

Screening = Not Screened
TX = TX Level
TXV = TXV Level
S = S Level

Package Type

_ = Axial Leaded

SMS = Surface Mount Square Tab

Family/Voltage

60 = 600 V 70 = 700 V 80 = 800 V

90 = 900 V

SHF1160 & SHF1160SMS thru SHF1190 & SHF1190SMS

30 nsec 1 Amp Hyper Fast Rectifier 600 - 900 V

Features:

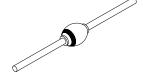
- Hyper fast recovery: 30 nsec maximum
- PIV to 900 Volts, consult factory for higher voltages
- Low reverse leakage current
- · Hermetically sealed
- Void free construction
- For high efficiency applications
- Higher voltages available consult factory
- TX, TXV, and S level screening available^{2/}

Maximum Ratings		Symbol	Value	Units
Peak Repetitive Reverse and DC Blocking	SHF1160 SHF1170 SHF1180 SHF1190	V _{RRM} V _{RSM} V _R	600 700 800 900	Volts
Average Rectified Forward Current (Resistive Load, 60 Hz Sine Wave, T _A = 25°C)		I _O	1.0	Amps
Peak Surge Current (8.3 ms Pulse, Half Sine Wave, T _A = 25°C)		I _{FSM}	25	Amps
Operating & Storage Temperature		T _{OP} & T _{STG}	-65 to +175	°C
Maximum Thermal Resistance	Junction to Leads, L = 3/8 Junction to Tabs	$R_{\theta JE}$	50 28	°C/W

NOTES: Axial Lead Diode SMS

1/ For ordering information, price, and availability - contact factory.

2/ Screening based on MIL-PRF-19500. Screening flows available on request.





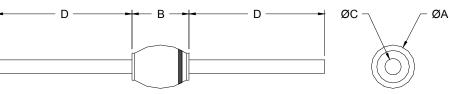


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SHF1160 & SHF1160SMS thru SHF1190 & SHF1190SMS

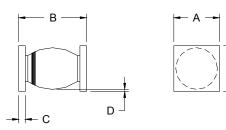
Electrical Characteristic	Symbol	Max	Units
Instantaneous Forward Voltage Drop ($I_F = 1A_{DC}$, $T_A = 25$ °C pulsed)	V _F	1.9	V_{DC}
Instantaneous Forward Voltage Drop (I _F = 1A _{DC} , T _A = -55°C pulsed)	V _F	2.4	V_{DC}
Reverse Leakage Current (Rated V_R , $T_A = 25$ °C pulsed)	I _R	10	μΑ
Reverse Leakage Current (Rated V _R , T _A = 100°C pulsed)	I _R	200	μΑ
Reverse Recovery Time (I _F = 500 mA, I _R = 1 A, I _{RR} = 250 mA, T _A = 25 °C)	t _{RR}	30	nsec
Junction Capacitance (V _R = 10V _{DC} , T _A = 25°C, f = 1MHz)	CJ	18	pF





DIM	MIN	MAX
Α	0.100"	0.135"
В	0.130"	0.185"
С	0.027"	0.033"
D	1.00"	

Case Outline: (SMS)



DIM	MIN	MAX
Α	0.140"	0.155"
В	0.180"	0.230"
С	0.020"	0.030"
D	0.002"	